AMENDMENTS TO THE CLIAMS

Claim 1 (original): A semiconductor light emitting device comprising:

a semiconductor lamination portion formed by laminating at least an n-type layer and a p-type layer made of gallium nitride based compound semiconductor so as to form a light emitting portion;

a light transmitting conductive layer formed on a surface of the semiconductor lamination portion; and

an upper electrode formed so as to be in contact with an exposed surface of the semiconductor lamination portion formed by removing a part of the light transmitting conductive layer, and with the light transmitting conductive layer,

wherein an electric current blocking means is formed on the exposed surface of the semiconductor lamination portion which is formed by removing a part of the light transmitting conductive layer, thereby preventing electric current from flowing into a part under the upper electrode while ensuring good adhesion between the upper electrode and the surface of the semiconductor lamination portion.

Claim 2 (original): The semiconductor light emitting device according to claim 1, wherein the electric current blocking means is a recessed portion formed on the exposed surface of the semiconductor lamination portion which is formed by removing the light transmitting conductive layer.

Claim 3 (original): The semiconductor light emitting device according to claim 1, wherein the electric current blocking means is an oxygen containing layer formed on the exposed surface of the semiconductor lamination portion which is formed by removing the light transmitting conductive layer.

Claim 4 (currently amended): The semiconductor light emitting device according to claim ~~3~~ 2, wherein the recessed portion is formed with a depth of 10 to 50 nm.

Claim 5 (original): A method for manufacturing a semiconductor light emitting device comprising steps of:

forming a semiconductor lamination portion by laminating gallium nitride based compound semiconductor layers so as to form a light emitting portion including an n-type layer and a p-type layer on a substrate;

forming a light transmitting conductive layer on the semiconductor lamination portion;

exposing a surface of the semiconductor lamination portion by etching a part of the light transmitting conductive layer where an upper electrode is planning to be formed;

forming an electric current blocking means by exposing the exposed surface of the semiconductor lamination portion which is exposed by the etching to oxygen plasma; and

forming an upper electrode so as to adhere to the exposed surface of the semiconductor lamination portion formed as the electric current blocking means and to a vicinity of an opening of the light transmitting conductive layer.

Claim 6 (original): The method for manufacturing a semiconductor light emitting device according to claim 5, further comprising the steps instead of the steps of exposing to the oxygen plasma and forming the upper electrode:

forming a recessed portion on the exposed surface of the semiconductor lamination portion by a dry etching; and

forming an upper electrode so as to adhere to an exposed surface in the recessed portion and to a vicinity of an opening of the light transmitting conductive layer.

Claim 7 (original): The method for manufacturing a semiconductor light emitting device according to claim 5, wherein treating by the oxygen plasma is applied with a plasma source power of 200 to 400 W for 5 to 30 minutes.